

ECE321 – Electronics I

Lecture 21: Combinational Logic: NAND & NOR Gate

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Review of Last Lecture

Layout Techniques

- **Design for density**
- **Design for performance**
- **Design for reliability**

Today's Lecture

NAND Gate

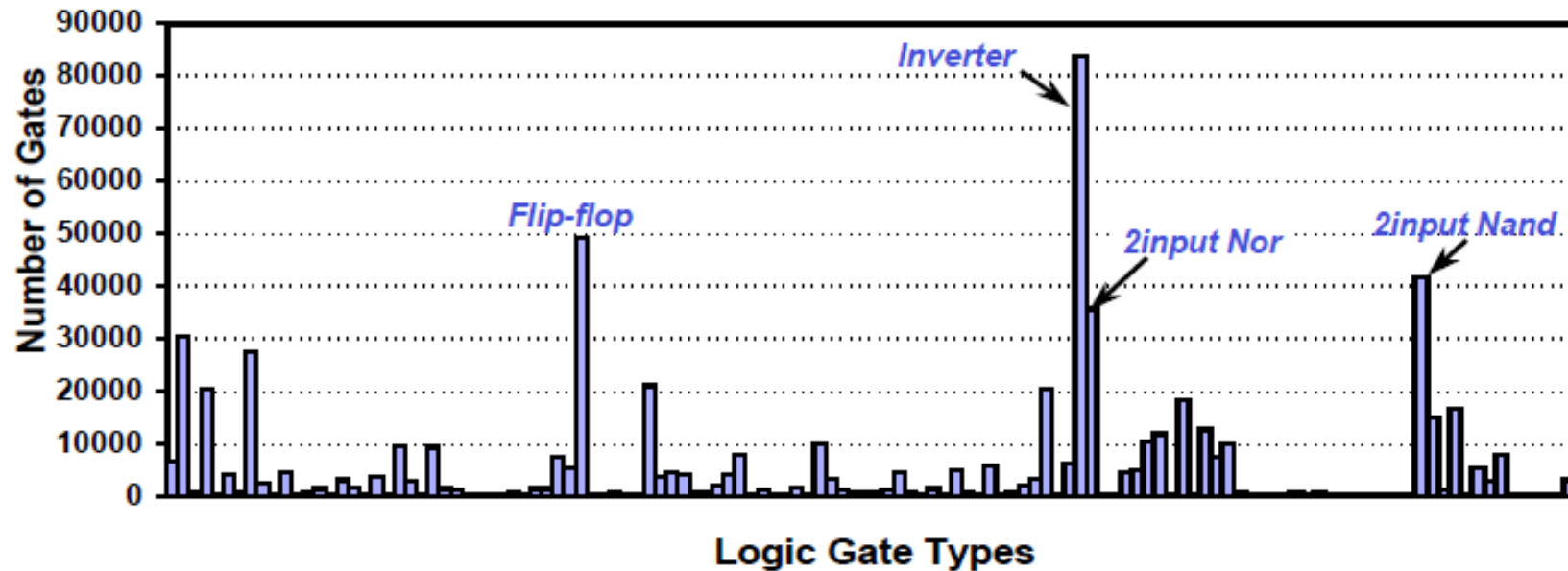
- **Basic circuit for CMOS NAND Gate**
- **Circuit analysis techniques**
- **Proper transistor sizing**

NOR Gate

- **Basic circuit for CMOS NOR Gate**
- **Circuit analysis techniques**
- **Proper transistor sizing**

Different Types of Logic Gates

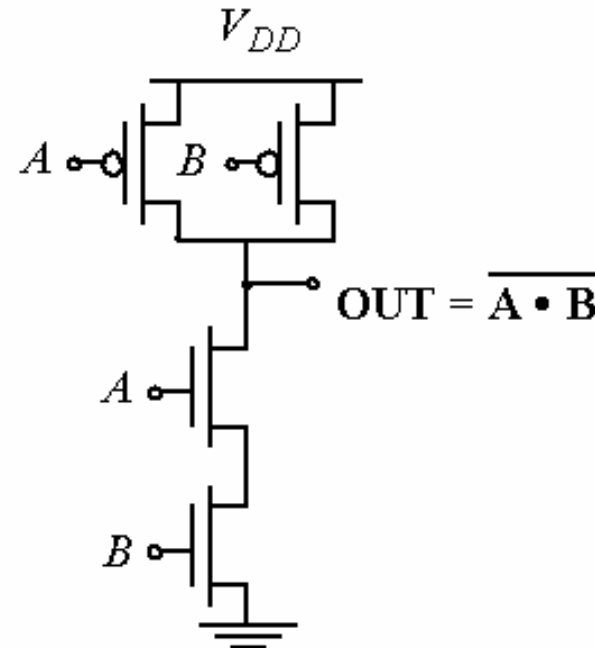
- Besides Inverter and Flip-Flop, the most used logic gates in digital circuits are NAND and NOR gates



CMOS NAND Gate Structure

A	B	Out
0	0	1
0	1	1
1	0	1
1	1	0

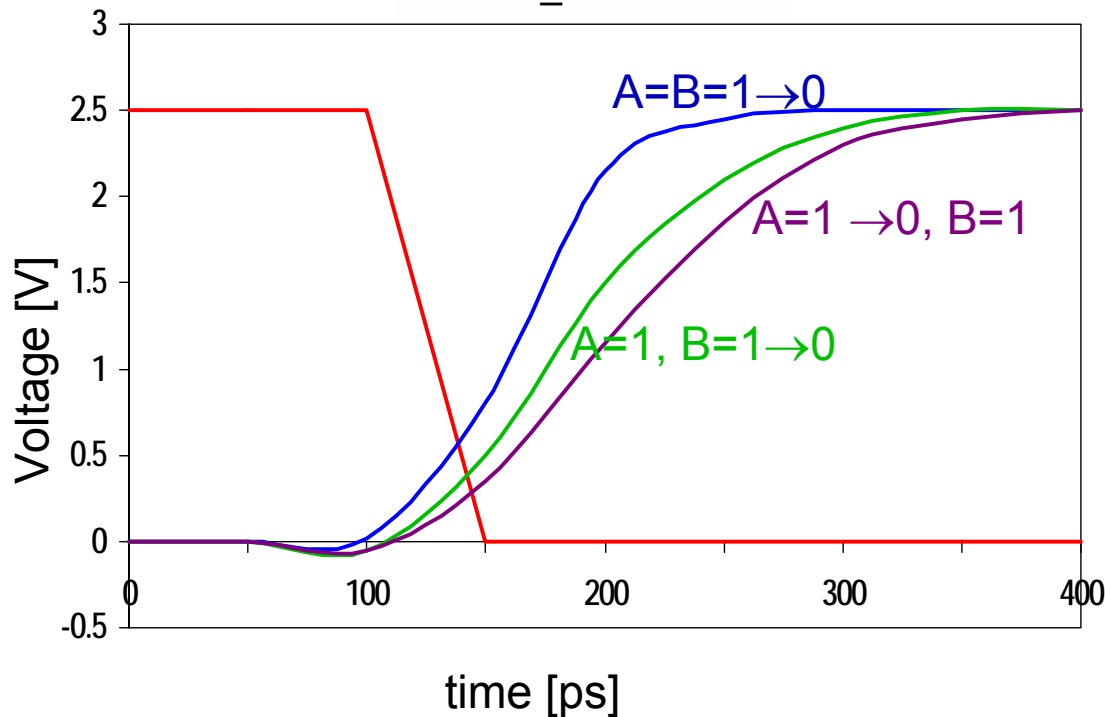
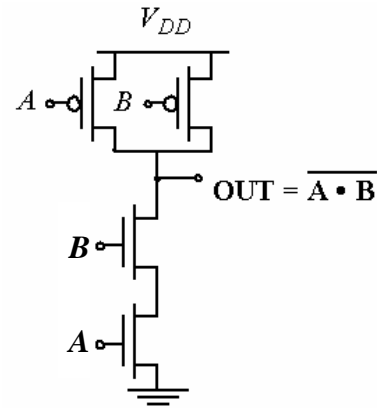
Truth Table of a 2 input NAND gate



PUN: $\overline{A} + \overline{B} = \overline{A \cdot B}$ (Conduction to VDD)

PDN: AB (Conduction to GND)

NAND Gate Dynamic Behavior

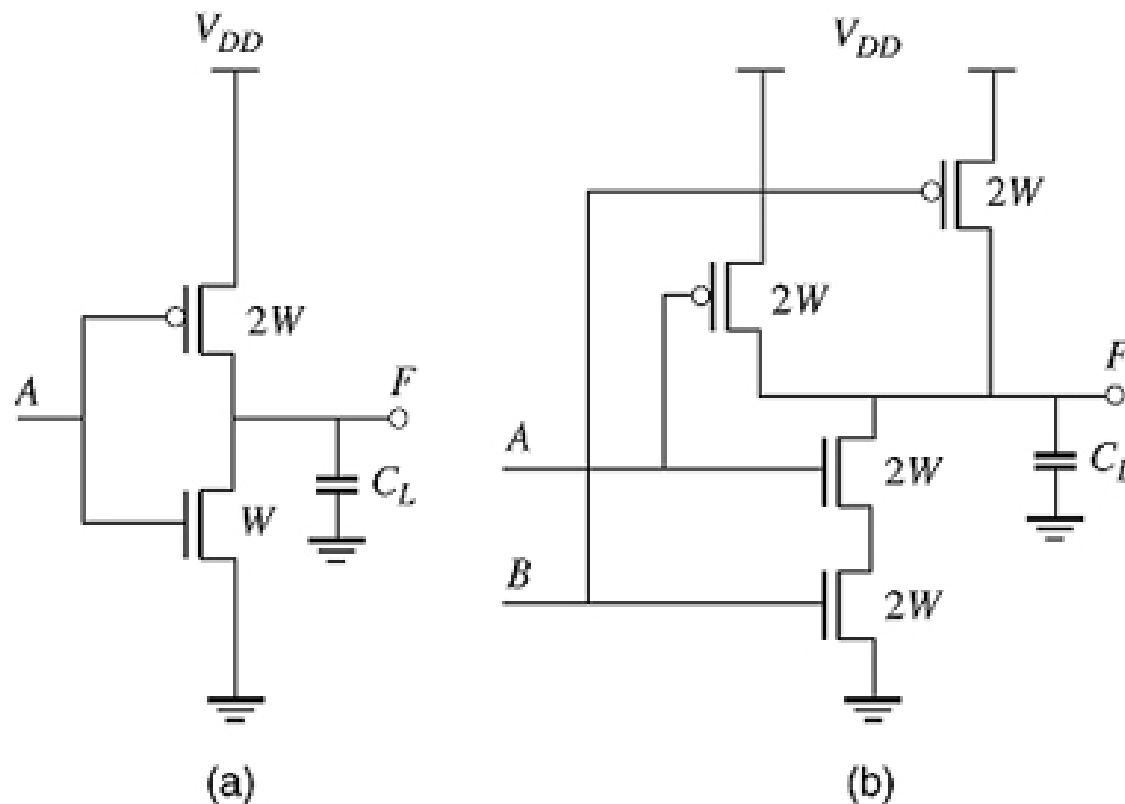


Input Data Pattern	Delay (psec)
A=B=0→1	67
A=1, B=0→1	64
A= 0→1, B=1	61
A=B=1→0	45
A=1, B=1→0	80
A= 1→0, B=1	81

NMOS = $0.5\mu\text{m}/0.25\mu\text{m}$
 PMOS = $0.75\mu\text{m}/0.25\mu\text{m}$
 $C_L = 100\text{ fF}$

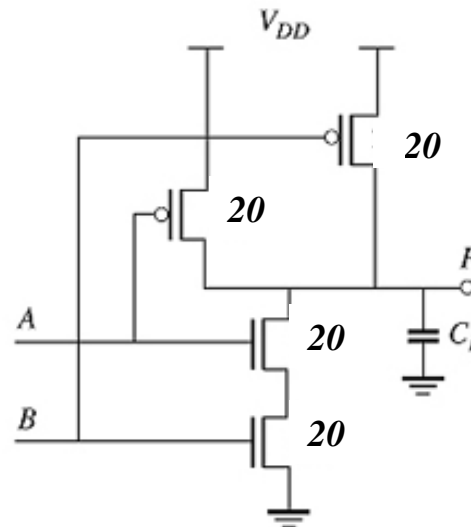
NAND versus Inverter Equivalency

- Use the series and parallel transistor model to normalize the worst case delay



Circuit Analysis for NAND Gate

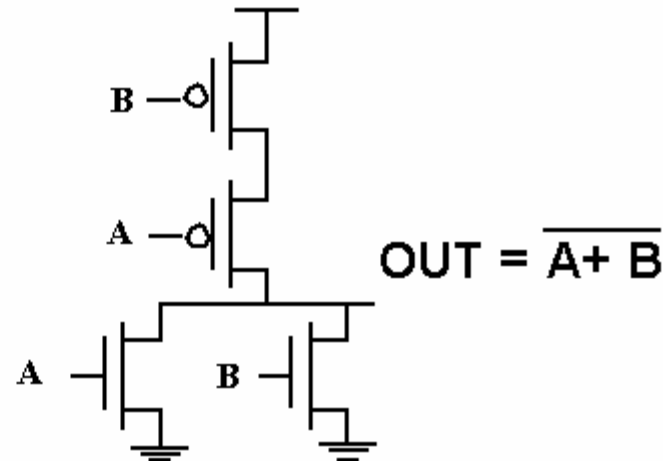
- ❑ To analyze NAND gate for delay, power, and VTC, use the same concepts you have learned for inverter.
- ❑ Example: A CMOS NAND gate with $V_{DD}=5V$ is designed such that $(W/L)_n = (W/L)_p = 20$. Assume that $V_{Tn}=0.7$, $V_{Tp}=-0.6$, $K'_n=100 \mu A/V^2$, $K'_p=-60 \mu A/V^2$, and the load capacitance is 100fF. Use the constant current source model to find:
 - 1) t_{pHL} , when $A=B=0 \rightarrow 1$
 - 2) t_{pLH} , when $A=B=1 \rightarrow 0$
 - 3) t_{pLH} , when $A=1$ and $B=1 \rightarrow 0$



CMOS NOR Gate

A	B	Out
0	0	1
0	1	0
1	0	0
1	1	0

Truth Table of a 2 input NOR gate



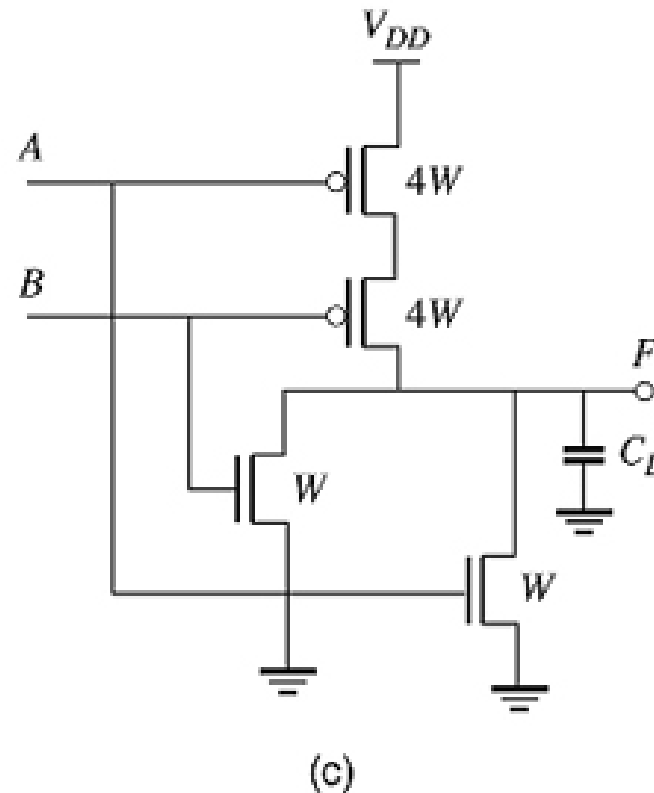
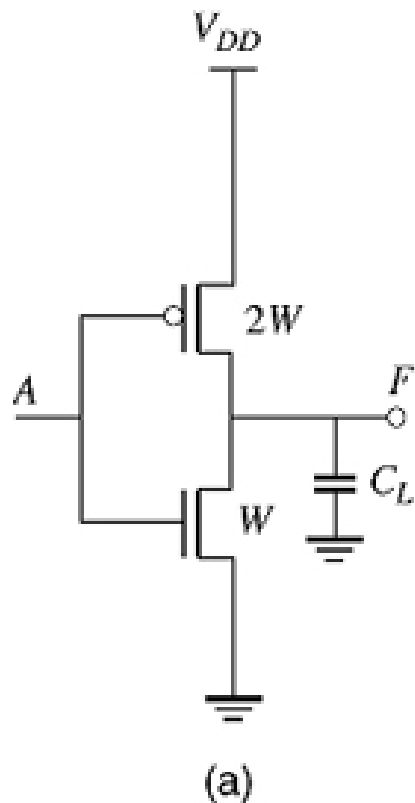
PUN: $\overline{A} \cdot \overline{B} = \overline{A+B}$ (Conduction to VDD)

PDN: $A+B$ (Conduction to GND)

- ❑ How do you size transistors to have approximately the same delay as an inverter?
- ❑ Which one is better to use often: NOR or NAND?

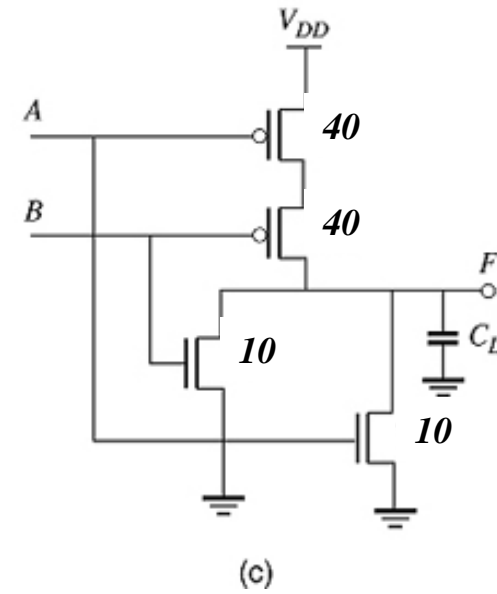
NOR versus Inverter Equivalency

- Use the series and parallel transistor model to normalize the worst case delay



Circuit Analysis for NOR Gate

- ❑ To analyze NOR gate for delay, power, and VTC, use the same concepts you have learned for inverter.
- ❑ Example: A CMOS NOR gate with $V_{DD}=5V$ is designed such that $(W/L)_n = 10$ and $(W/L)_p = 40$. Assume that $V_{Tn}=0.7$, $V_{Tp}=-0.6$, $K'_n=100 \mu A/V^2$, and $K'_p=-60 \mu A/V^2$.
 - 1) Find the switching threshold voltage, when A and B are tied together
 - 2) Find maximum I_{DD} for this NOR gate



Circuit Configuration

- ❑ To analyze a logic circuit, you may need to set other inputs (vectors) to be able to pass a transition.
- ❑ This is the main approach for testing a digital circuit.
- ❑ Example:

Write the binary sequence for $AB\ CD\ E$ that will

(a) Make $F = f(D)$

(b) Make $F = f(A)$

